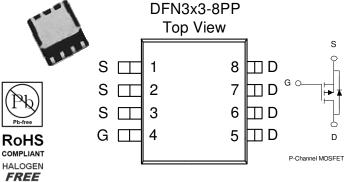
P-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low r _{DS(on)} provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$		
100	$269 @ V_{GS} = -10V$	-3		
-100	289 @ V _{GS} = -5.5V	-2.9		



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage			-100	V		
Gate-Source Voltage		V_{GS}	±20	V		
	T _A =25°C	T_	-3			
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	-2.5	A		
Pulsed Drain Current ^b	I_{DM}	±50				
Continuous Source Current (Diode Conduction) ^a		I_S	-2.1	A		
D D: : .: a	$T_A=25^{\circ}C$	D	3.5	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	r D	2.0	VV		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
a	t <= 10 sec	ъ	35	°C/W		
Maximum Junction-to-Ambient ^a	Steady State	R _{0JA}	81	°C/W		

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM7101P

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Cymbol	Took Conditions	Limits			Unit	
Parameter	Symbol	Test Conditions	Min	Тур	Max	ווויטן	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1			٧	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА	
Zero date voltage Brain ourient	USS	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5	μΛ	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			Α	
Duein Course On Besisters A	r	$V_{GS} = -10 \text{ V}, I_{D} = -1 \text{ A}$			269	mΩ	
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = -5.5 \text{ V}, I_D = -1 \text{ A}$			289	11122	
Forward Tranconductance ^A	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -1 \text{ A}$		29		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8		٧	
Dynamic ^b	•						
Total Gate Charge	Q_g	V 45V V 55V		8			
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -5.5 \text{ V},$ $I_{D} = -1 \text{ A}$		3		nC	
Gate-Drain Charge	Q_{gd}	1D = -1 A		3			
Input Capacitance	C _{iss}			1300			
Output Capacitance	C _{oss}	V_{DS} =-15V, V_{GS} =0V, f=1MHz		130		pF	
Reverse Transfer Capacitance	C_{rss}			70			
Turn-On Delay Time	$t_{d(on)}$			5			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, \text{ R}_{L} = 6 \Omega ,$ $I_{D} = -1 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}$		4		nS	
Turn-Off Delay Time	t _{d(off)}			60			
Fall-Time	t _f			40			

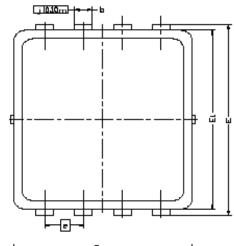
Notes

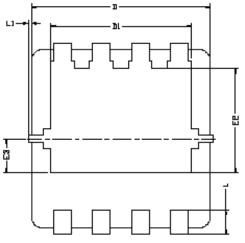
a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

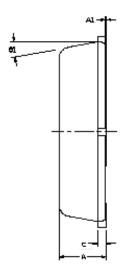
b. Guaranteed by design, not subject to production testing.

Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.

Package Information







DIM.	MILLIMETERS			INCHES				
יויונת	MIN	NOM	MAX	MIN	NDM	MAX		
Α	0,700	0'80	0.900	0.0276	0.0315	0.0354		
A1	0.00	-	0.05	0.000	-	0.002		
la	0.24	0.30	0.35	0.009	0.012	0.014		
C	0.10	0.152	0,25	0,004	0,006	0,010		
ם	(3	3.00 BSC			0.118 BSC			
D1	2.35 BSC 0.093 BSC				C 2			
Ε	3,20 BSC			0,	126 BS)C		
E1	3	3.00 B2C 0.118 B2C			C			
E5	1.75 BSC			0.069 BSC				
E3	0.575 BSC			0.	023 BS	C.		
6	0.65 BSC			O.	026 BS	C 2		
L	0,30	0,40	0,50	0.0118	0.0157	0.0197		
L1			0.100	D		0.004		
91	٥°	10*	12*	0*	10°	12*		